

AMENDMENTS TO THE CLAIMS

1. (Currently amended) An electrode for incorporation in a solar cell, the electrode comprising a mixture of carbon carrying a metal and a binder, the carbon having a specific surface area equal to or larger than $100 \text{ m}^2/\text{g}$, and the metal is at least one metal selected from the group consisting of Pt, Ru, Co, Ti, Ni, Al and Au.

2. (Original) The electrode according to claim 1, which is formed on an electrically conductive substrate.

3. (Original) The electrode according to claim 2 wherein the electrically conductive substrate is made of glass, a polymer film or a metal.

4. (Original) The electrode according to claim 1 wherein the carbon is needle-like carbon, fullerene, carbon nanotube or electrically conductive carbon black.

5. (Canceled)

6. (Canceled)

7. (Original) The electrode according to claim 1 wherein the specific surface area of the carbon is equal to or larger than $300 \text{ m}^2/\text{g}$.

8. (Original) The electrode according to claim 1 wherein the amount of the metal carried by the carbon is equal to or more than 5 weight percent of the carbon.

9-15. (Canceled)

16. (Previously Presented) The electrode according to claim 1, wherein the electrode is disposed immediately adjacent to an electrolytic layer.

17. (Previously Presented) The electrode according to claim 1, wherein the binder is insoluble to electrolytes.

18. (Currently amended) An electrode for incorporation in a solar cell, the electrode comprising a mixture of carbon carrying both a metal and a binder, wherein the metal is at least one metal selected from the group consisting of Pt, Ru, Co, Ti, Ni, Al and Au and the amount of metal in the electrode ranges between 5 wt % and 15 wt % relative to the carbon.

19. (Previously presented) The electrode according to claim 1, wherein the binder in the electrode comprises more than 5 wt % of the carbon.

20. (Previously presented) The electrode according to claim 1, further comprising an electrolytic layer disposed adjacent to the electrode and a semiconductor layer disposed adjacent to the electrolytic layer, the electrolytic layer having a thickness of between about 1 micron and 100 microns.